

**VIA HAND DELIVERY**

#14  
9/10/03  
PATENT  
J. G. G. G.

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Appl No.	: 09/994,511	Confirmation No.	: 1533
Applicants	: Kie Y. Ahn; Leonard Forbes	Attorney Docket No.:	500466.02 (29356/US/1)
Filed	: November 26, 2001	Customer No.	: 27,076
Art Unit	: 2879	Issue Fee Paid	: July 3, 2003
Examiner	: Kenneth J. Ramsey		
Title	: FIELD EMISSION DISPLAY HAVING REDUCED POWER REQUIREMENTS AND METHOD		

**INFORMATION DISCLOSURE STATEMENT**

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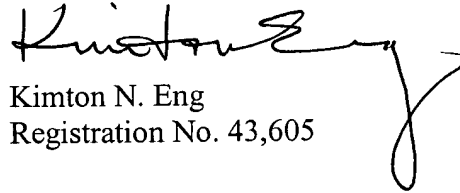
Sir:

In accordance with 37 C.F.R. §§ 1.56 and 1.97 through 1.98, applicants wish to make known to the Patent and Trademark Office the references set forth on the attached form PTO-1449 (copies of the cited references, as required under 37 C.F.R. § 1.98, are enclosed). Although the aforesaid references are made known to the Patent and Trademark Office in compliance with applicants' duty to disclose all information they are aware of which is believed relevant to the examination of the above-identified application, applicants believe that their invention is patentable.

Please acknowledge receipt of this Information Disclosure Statement and kindly make the cited references of record in the above-identified application.

Respectfully submitted,

DORSEY & WHITNEY LLP



Kimton N. Eng  
Registration No. 43,605

SHA:mp/pep

Enclosures:

Form PTO-1449

Cited References (37)

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FORM PTO-1449 (REV. 7-80)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. <b>500466.02</b>		APPLICATION NO. <b>09/994,511</b>	
<b>INFORMATION DISCLOSURE STATEMENT</b> <i>(Use several sheets if necessary)</i>				APPLICANT(S) <b>Kie Y Ahn; Leonard Forbes</b>		GROUP ART UNIT <b>2879</b>	
				FILING DATE <b>November 26, 2001</b>			

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
AA	3,665,241	05/23/72	Spindt et al.	313	351		
AB	3,755,704	08/28/73	Spindt et al.	313	309		
AC	3,812,559	05/28/74	Spindt et al.	29	25		
AD	4,266,233	05/05/81	Bertotti et al.	357	22		
AE	5,142,184	8/25/92	Kane	313	309		
AF	5,194,780	3/16/93	Meyer	315	169.3		
AG	5,229,331	07/20/93	Doan et al.	437	228		
AH	5,259,799	11/09/93	Doan et al.	445	24		
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AK	5,483,067	01/09/96	Fujii et al.	250	338.3		
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AN	5,597,444	01/28/97	Gilton	156	643		
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AP	5,853,492	12/29/98	Cathey et al.	134	3		
AQ	5,712,534	1/27/98	Lee et al.	315	169.3		

FOREIGN PATENT DOCUMENTS							
DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION		
					YES	NO	
AR							

OTHER PRIOR ART <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>	
AS	Anderson, R.C. et al., "Porous Polycrystalline Silicon: A New Material for MEMS," <i>Journal of Microelectromechanical Systems</i> 3(1):10-18, 1994
AT	Boswell, E.C. et al., "Polycrystalline Silicon Field Emitters," 8 <sup>th</sup> International Vacuum Microelectronics Conference Technical Digest, pp. 181-186, 1996

EXAMINER	DATE CONSIDERED
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\* EXAMINER: Initial if reference considered, whether or not criteria is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).

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<b>OTHER PRIOR ART</b> <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>					
	BA	Boswell, E.C. et al., "Polycrystalline silicon field emitters," <i>J Vac Sci Technol. B</i> 14(3):1910-1913, 1996			
	BB	Huang, W.N. et al., "Photoluminescence in porous sputtered polysilicon films formed by chemical etching," <i>Semicond. Sci. Technol.</i> 12:228-233, 1997			
	BC	Huang, W.N. et al., "Properties of chemically etched porous polycrystalline silicon deposited by r.f. sputtering," <i>IEEE Hong Kong Electron Devices Meeting</i> , pp. 21-24, 1996			
	BD	Huq, S.E. et al., "Comparative study of gated single crystal silicon and polysilicon field emitters," <i>J. Vac. Sci. Technol. B</i> 15(6):2855-2858, 1997			
	BE	Huq, S.E. et al., "Fabrication of Gated Polycrystalline Silicon Field Emitters," 9 <sup>th</sup> International Vacuum Microelectronics Conference, St. Petersburg, pp. 367-370, 1996			
	BF	Kim, I.H. et al., "Metal FEAs on Double Layer Structure of Polycrystalline Silicon," 9 <sup>th</sup> International Vacuum Microelectronics Conference, St. Petersburg, pp. 423-426, 1996			
	BG	Kim, I.H. et al., "Fabrication of metal field emitter arrays on polycrystalline silicon," <i>J. Vac. Sci. Technol. B</i> 15(2):468-471, 1997			
	BH	Ku, T.K. et al., "Enhanced Electron Emission from Phosphorus-Doped Diamond-Clad Silicon Field Emitter Arrays," <i>IEEE Electron Device Letters</i> 17(5):208-210, 1996			
	BI	Lacher, F. et al., "Electron field emission from thin fine-grained CVD diamond films," <i>Diamond and Related Materials</i> 6:1111-1116, 1997			
	BJ	Lazarouk, S. et al., "Electrical characterization of visible emitting electroluminescent Schottky diodes based on n-type porous silicon and on highly doped n-type porous polysilicon," <i>Journal of Non-Crystalline Solids</i> 198-200:973-976, 1996			
	BK	Lee, J.H. et al., "A New Fabrication Method of Silicon Field Emitter Array with Local Oxidation of Polysilicon and Chemical-Mechanical-Polishing," 9 <sup>th</sup> International Vacuum Microelectronics Conference, St. Petersburg, pp. 415-418, 1996			
	BL	Lee, K.R. et al., "Field emission behavior of (nitrogen incorporated) diamond-like carbon films," <i>Thin Solid Films</i> 290-291:171-175, 1996			
	BM	Litovchenko, V.G. et al., "Emission Properties of the Silicon Cathodes Coated with Doped Diamond-Like Carbon Films," <i>IEEE International Conf. On Plasma Science</i> , p. 308, Abstract 7A02, 1997			
	BN	Pullen, S.E. et al., "Enhanced Field Emission from Polysilicon Emitters Using Porous Silicon," 9 <sup>th</sup> International Vacuum Microelectronics Conference, St. Petersburg, pp. 211-214, 1996			
	BO	Uh, H.S. et al., "Enhanced Electron Emission and Its Stability from Gated Mo-polycide Field Emitters," <i>IEEE</i> , pp. 713-716, 1997			
	BP	Uh, H.S. et al., "Fabrication and Characterization of Gated n+ Polycrystalline Silicon Field Emitter Arrays," 9 <sup>th</sup> International Vacuum Microelectronics Conference, St. Petersburg, pp. 419-422, 1996			
	BQ	Uh, H.S., "Process design and emission properties of gated n+ polycrystalline silicon field emitter arrays for flat-panel display applications," <i>J. Vac. Sci. Technol. B</i> 15(2):472-476, 1997			
	BR	Vaudaine, P. and Meyer, R., "Microtips Fluorescent Display," technical digest of IEDM 91, pp. 197-200, 1991			
EXAMINER				DATE CONSIDERED	
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